

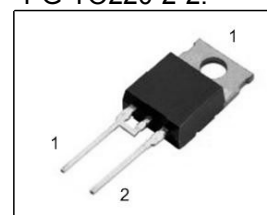
Silicon Carbide Schottky Diode

- Worlds first 600V Schottky diode
- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

thinQ!™ SiC Schottky Diode
Product Summary

V_{RRM}	600	V
Q_C	24	nC
I_F	8	A

PG-TO220-2-2.



Type	Package	Ordering Code	Marking	Pin 1	Pin 2
SDT08S60	PG-TO220-2-2.	Q67040S4647	D08S60	C	A

Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous forward current, $T_C=100^\circ\text{C}$	I_F	8	A
RMS forward current, $f=50\text{Hz}$	I_{FRMS}	11.3	
Surge non repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	I_{FSM}	26	
Repetitive peak forward current $T_j=150^\circ\text{C}$, $T_C=100^\circ\text{C}$, $D=0.1$	I_{FRM}	32	
Non repetitive peak forward current $t_p=10\mu\text{s}$, $T_C=25^\circ\text{C}$	I_{FMAX}	80	
i^2t value, $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	$\int i^2 dt$	3.4	A^2s
Repetitive peak reverse voltage	V_{RRM}	600	V
Surge peak reverse voltage	V_{RSM}	600	
Power dissipation, $T_C=25^\circ\text{C}$	P_{tot}	65	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$

⁰⁾J-STD20 and JESD22

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	2.3	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

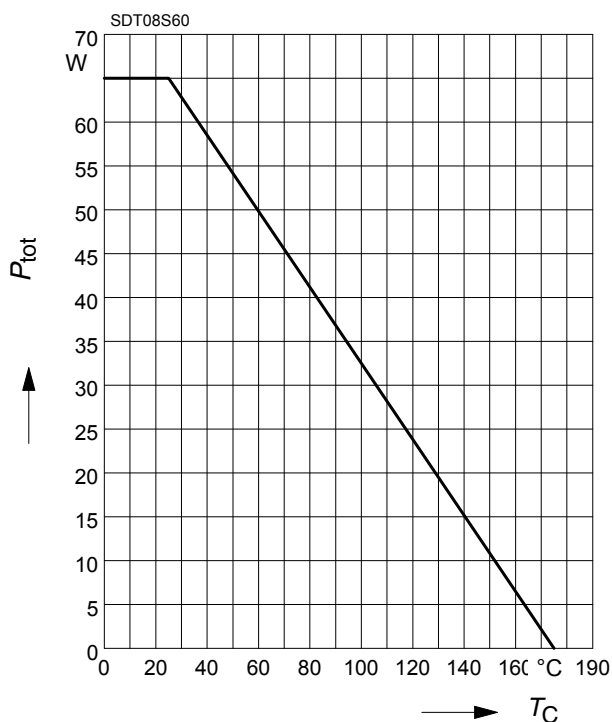
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Diode forward voltage $I_F=8A, T_j=25^{\circ}C$ $I_F=8A, T_j=150^{\circ}C$	V_F	- -	1.5 1.7	1.7 2.1	V
Reverse current $V_R=600V, T_j=25^{\circ}C$ $V_R=600V, T_j=150^{\circ}C$	I_R	- -	28 70	300 1500	μA

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Total capacitive charge $V_R=400V, I_F=8A, di_F/dt=200A/\mu s, T_J=150^{\circ}C$	Q_C	-	24	-	nC
Switching time $V_R=400V, I_F=8A, di_F/dt=200A/\mu s, T_J=150^{\circ}C$	t_{rr}	-	n.a	-	ns
Total capacitance $V_R=0V, T_C=25^{\circ}C, f=1MHz$ $V_R=300V, T_C=25^{\circ}C, f=1MHz$ $V_R=600V, T_C=25^{\circ}C, f=1MHz$	C	- - -	280 26 18	- - -	pF

1 Power dissipation

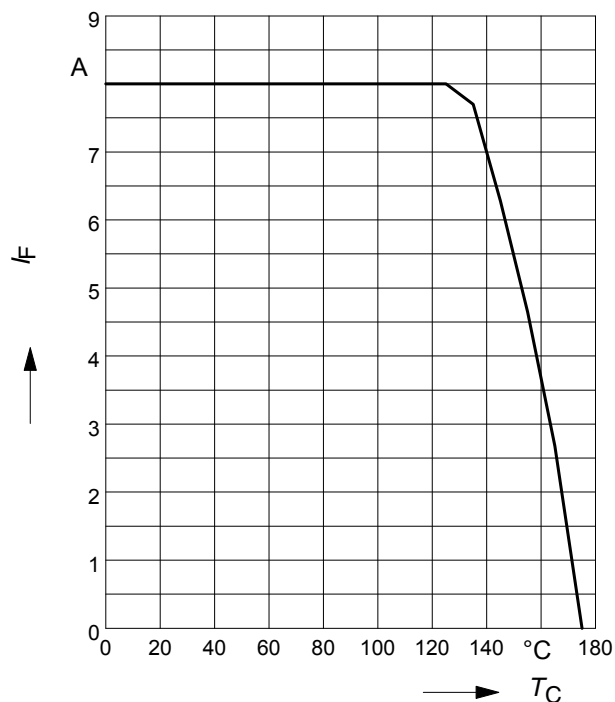
$$P_{\text{tot}} = f(T_C)$$



2 Diode forward current

$$I_F = f(T_C)$$

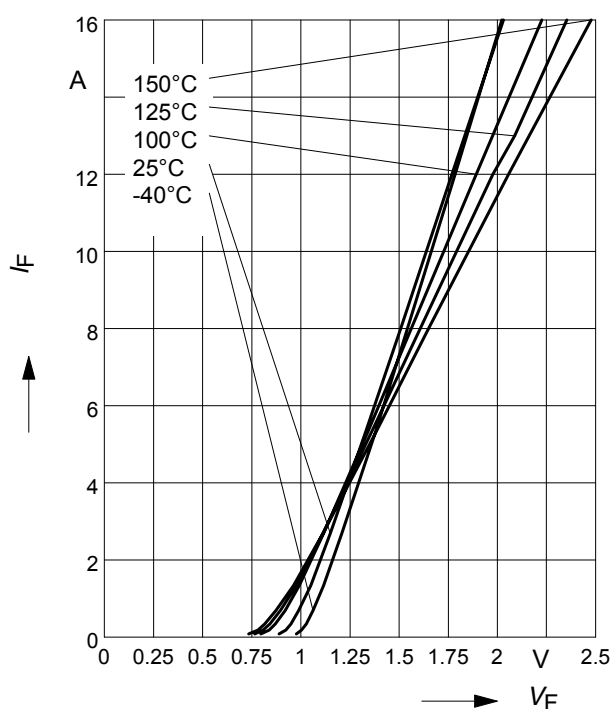
parameter: $T_j \leq 175^\circ\text{C}$



3 Typ. forward characteristic

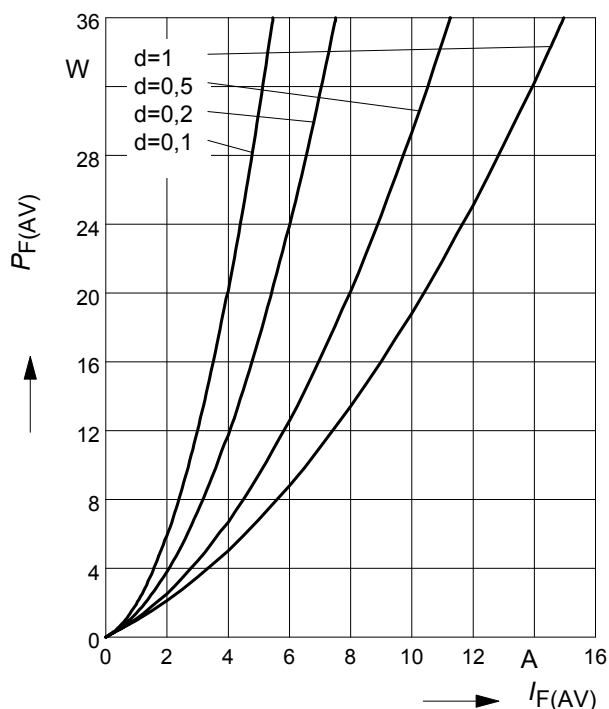
$$I_F = f(V_F)$$

parameter: T_j , $t_p = 350 \mu\text{s}$



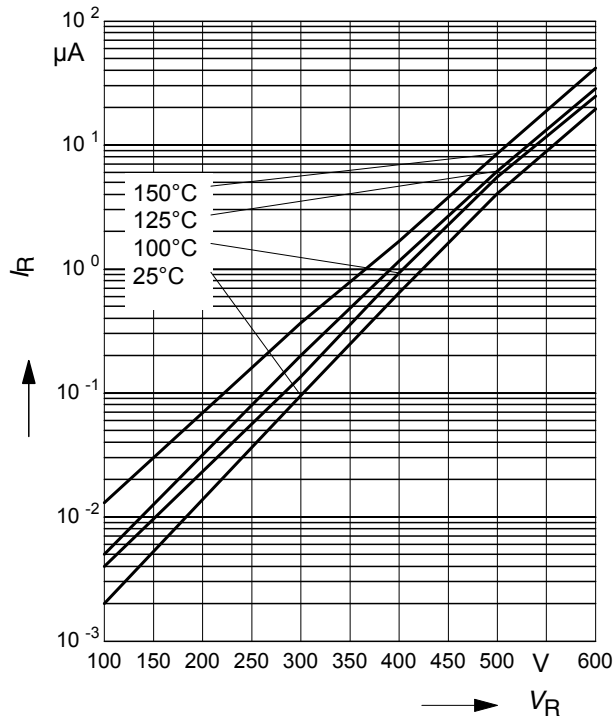
4 Typ. forward power dissipation vs. average forward current

$$P_{F(AV)} = f(I_F) \quad T_C = 100^\circ\text{C}, d = t_p/T$$



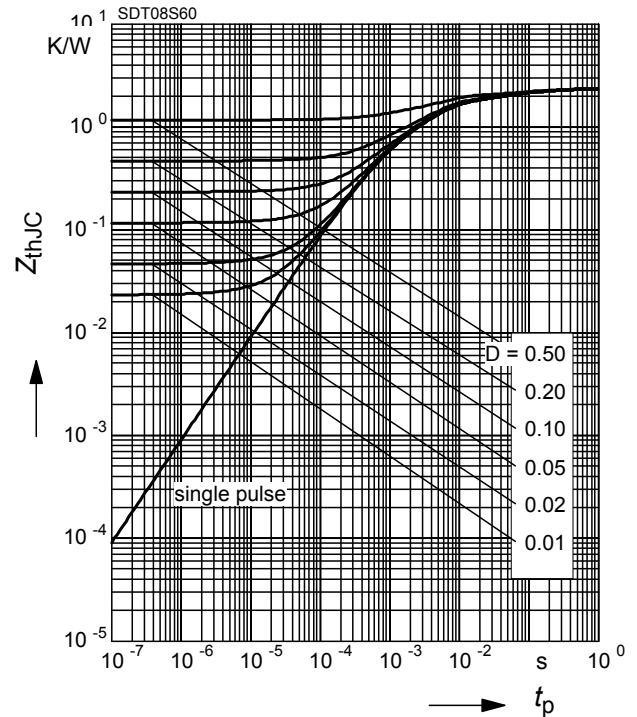
5 Typ. reverse current vs. reverse voltage

$$I_R = f(V_R)$$


6 Transient thermal impedance

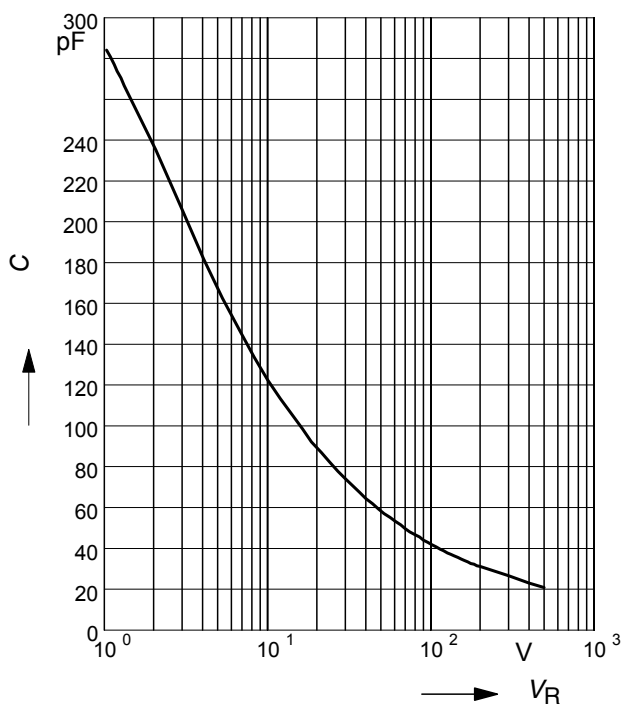
$$Z_{thJC} = f(t_p)$$

$$\text{parameter: } D = t_p / T$$

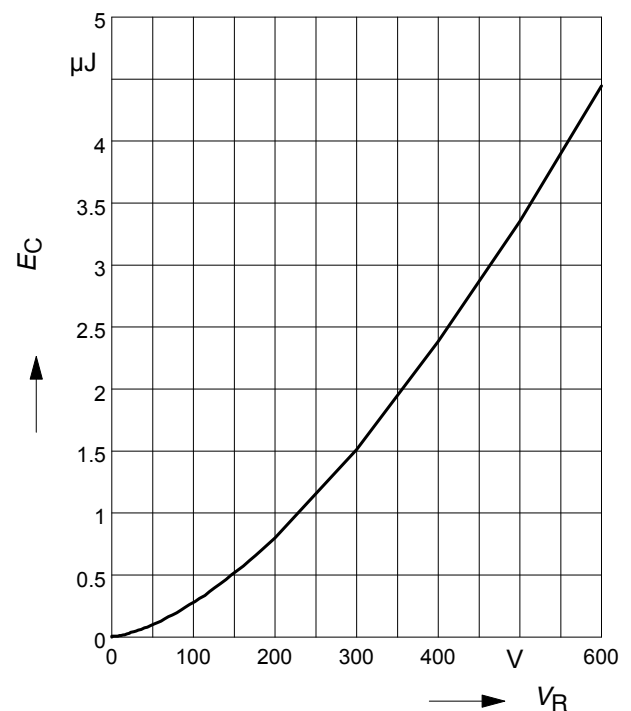

7 Typ. capacitance vs. reverse voltage

$$C = f(V_R)$$

parameter: $T_C = 25^\circ C$, $f = 1$ MHz


8 Typ. C stored energy

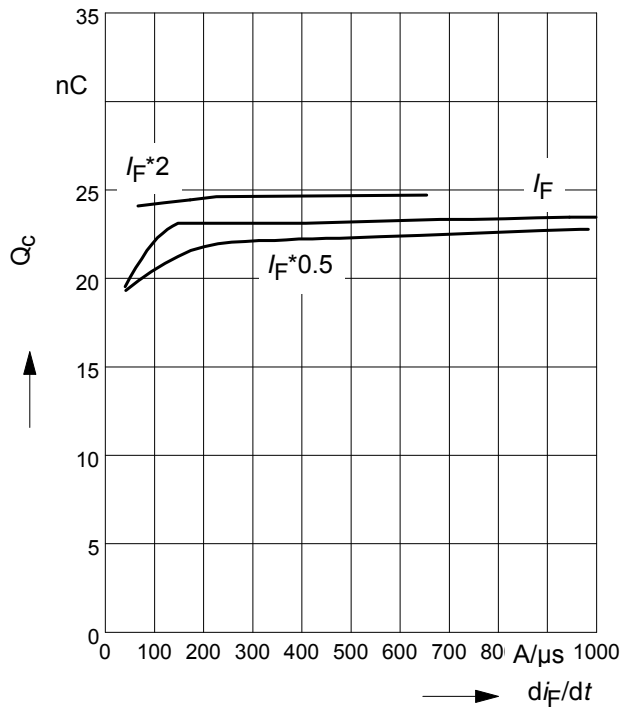
$$E_C = f(V_R)$$



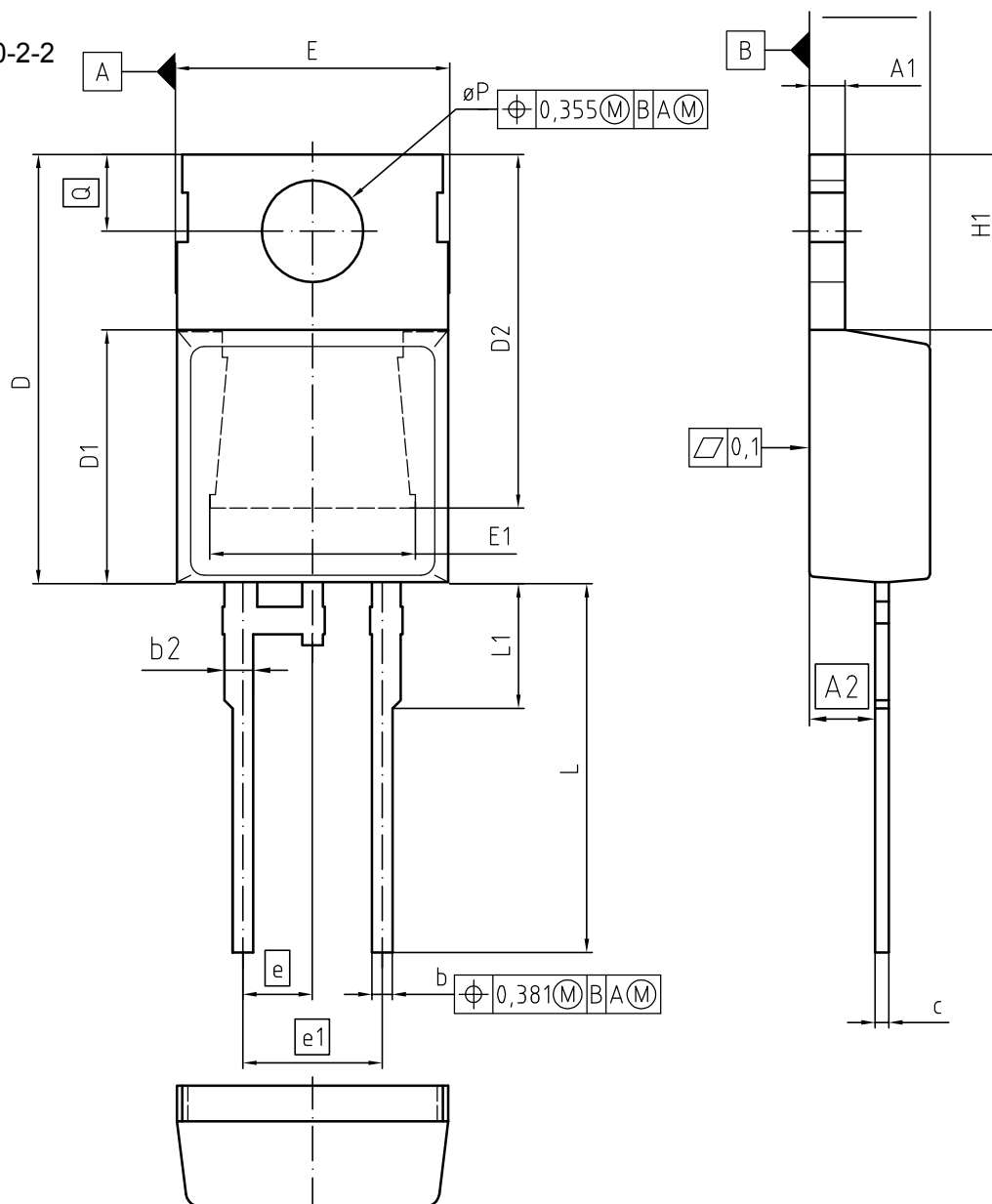
9 Typ. capacitive charge vs. current slope

$$Q_C = f(di_F/dt)$$

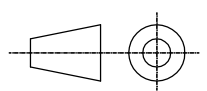
parameter: $T_j = 150\text{ °C}$



PG-TO-220-2-2



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.191	4.699	0.165	0.185
A1	1.170	1.400	0.046	0.055
A2	2.215	2.718	0.087	0.107
b	0.635	0.889	0.025	0.035
b2	0.950	1.651	0.037	0.065
c	0.330	0.635	0.013	0.025
D	14.808	15.950	0.583	0.628
D1	8.509	9.450	0.335	0.372
D2	12.850	14.245	0.506	0.561
E	9.677	10.363	0.381	0.408
E1	6.500	8.788	0.256	0.346
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H1	5.900	6.900	0.232	0.272
L	12.700	14.000	0.500	0.551
L1	3.048	4.800	0.120	0.189
øP	3.550	3.886	0.140	0.153
Q	2.540	3.048	0.100	0.120

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